

# SLA5003

N-channel

With built-in flywheel diode

External dimensions A...SLA

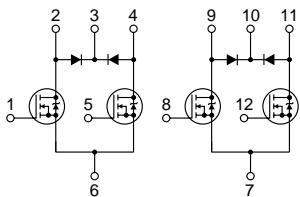
## Absolute maximum ratings

(Ta=25°C)

Symbol	Ratings	Unit
V <sub>DSS</sub>	200	V
V <sub>GSS</sub>	±20	V
I <sub>D</sub>	±5	A
I <sub>D(pulse)</sub>	±10 (PW≤1ms)	A
E <sub>AS*</sub>	60	mJ
I <sub>F</sub>	5(PW≤0.5ms, Du≤25%)	A
I <sub>FSM</sub>	10(PW≤10ms, Single pulse)	A
V <sub>R</sub>	200	V
P <sub>T</sub>	5 (Ta=25°C, with all circuits operating, without heatsink) 35 (Tc=25°C, with all circuits operating, with infinite heatsink)	W
θ <sub>j-a</sub>	25 (Junction-Air, Ta=25°C, with all circuits operating)	°C/W
θ <sub>j-c</sub>	3.57 (Junction-Case, Tc=25°C, with all circuits operating)	°C/W
V <sub>iso</sub>	1000 (Between fin and lead pin, AC)	Vrms
T <sub>ch</sub>	150	°C
T <sub>tsg</sub>	-40 to +150	°C

\* : V<sub>DD</sub>=20V, L=10mH, I<sub>D</sub>=3.5A, unclamped, see Fig. E on page 15.

## Equivalent circuit diagram



## Electrical characteristics

(Ta=25°C)

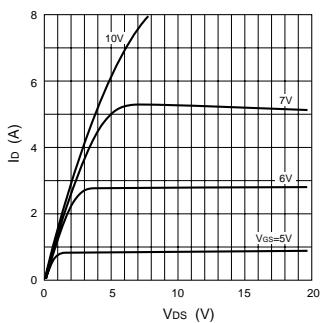
Symbol	Specification			Unit	Conditions
	min	typ	max		
V <sub>(BR)DSS</sub>	200			V	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V
I <sub>GSS</sub>			±500	nA	V <sub>GS</sub> =±20V
I <sub>DSS</sub>			250	μA	V <sub>Ds</sub> =200V, V <sub>GS</sub> =0V
V <sub>TH</sub>	2.0		4.0	V	V <sub>Ds</sub> =10V, I <sub>D</sub> =250μA
R <sub>e(yfs)</sub>	1.3	2.5		S	V <sub>Ds</sub> =10V, I <sub>D</sub> =5A
R <sub>Ds(ON)</sub>		0.67	0.9	Ω	V <sub>GS</sub> =10V, I <sub>D</sub> =5A
C <sub>iss</sub>	260			pF	V <sub>Ds</sub> =25V, f=1.0MHz,
C <sub>oss</sub>	100			pF	V <sub>GS</sub> =0V
t <sub>on</sub>	50			ns	I <sub>D</sub> =5A, V <sub>DD</sub> =100V, V <sub>GS</sub> =10V,
t <sub>off</sub>	60			ns	see Fig. 3 on page 16.
V <sub>SD</sub>		1.1	1.5	V	I <sub>SD</sub> =5A, V <sub>GS</sub> =0V
t <sub>rr</sub>		700		ns	I <sub>SD</sub> =±100mA

## Diode for flyback voltage absorption (1 circuit)

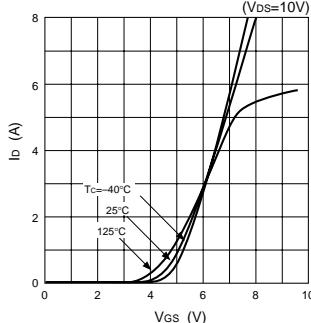
Symbol	Specification			Unit	Conditions
	min	typ	max		
V <sub>R</sub>	200			V	I <sub>R</sub> =10μA
V <sub>F</sub>		1.0	1.2	V	I <sub>F</sub> =1A
		1.5	2.0	V	I <sub>F</sub> =5A
I <sub>R</sub>			10	μA	V <sub>R</sub> =200V
t <sub>rr</sub>		100		ns	I <sub>F</sub> =±100mA

## Characteristic curves

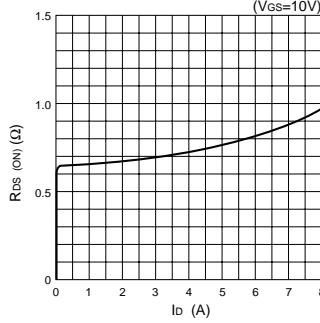
### ID-VDS Characteristics (Typical)



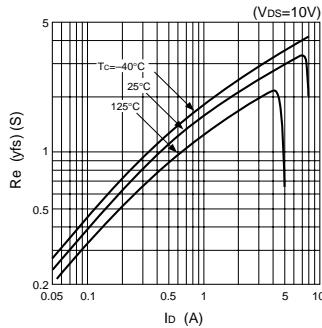
### ID-VGS Characteristics (Typical)



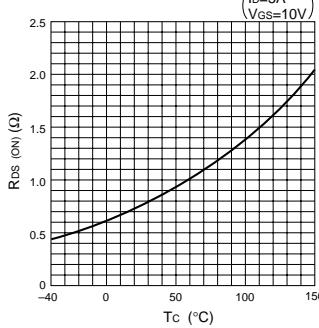
### RDS(ON)-ID Characteristics (Typical)



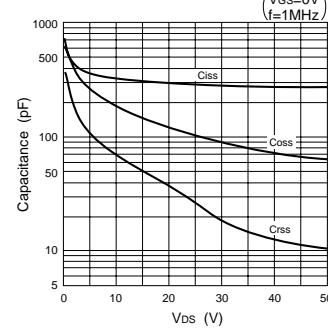
### Re(yfs)-Id Characteristics (Typical)



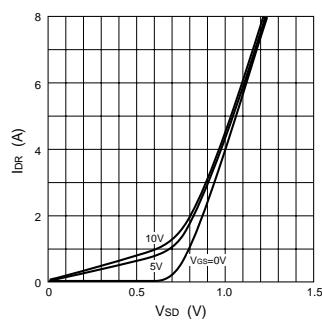
### RDS(ON)-Tc Characteristics (Typical)



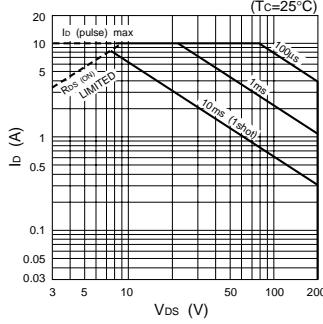
### Capacitance-VDS Characteristics (Typical)



### IDR-VSD Characteristics (Typical)



### Safe Operating Area (SOA)



### PT-Ta Characteristics

